

Amendments to the Specification:

On page 1, insert the following below the title:

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is the U.S. national phase of PCT application number PCT/EP2003/014010, filed September 18, 2003 and published in English under PCT Article 21(2), which further claims the benefit of Singapore patent application serial number 200205833-7 filed September 25, 2002. The entire disclosures of each of these applications are hereby incorporated by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

Please insert the following subheading prior to the paragraph beginning on page 1, l. 6, as shown below:

2. Background Art

Please insert the following subheading prior to the paragraph beginning on page 2, l. 1, as shown below:

SUMMARY OF THE INVENTION

Please insert the following subheading prior to the paragraph beginning on page 3, l. 1, as shown below:

BRIEF DESCRIPTION OF THE DRAWINGS

Please insert the following subheading prior to the paragraph beginning on page 3, l. 10, as shown below:

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT(S)

Please amend the paragraph (section) beginning on page 13, at line 15 as shown below:

The thickness of the low stress LTO layer and the high stress LTO layer is preferably between ~~1000 Å and 10000 Å~~ 1000 Å and 10000 Å.

Please amend the paragraph (section) beginning on page 14, at line 24 as shown below:

The thickness of the low stress LTO layer and the high stress LTO layer of the nn+ silicon epitaxial wafer is preferably between ~~1000 Å and 10000 Å~~ 1000 Å and 10000 Å.